



#### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	Rds(on)	I <sub>D</sub> T <sub>A</sub> = +25°C
	750mΩ @ V <sub>GS</sub> = -4.5V	-0.6A
-20V	1050mΩ @ V <sub>GS</sub> = -2.5V	-0.5A
	1500mΩ @ V <sub>GS</sub> = -1.8V	-0.45A

### **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

- DC-DC Converters
- Load Switch
- Power Management Functions





**SOT323** 

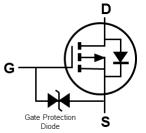
Top View

### **Features and Benefits**

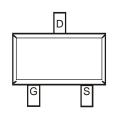
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

#### **Mechanical Data**

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed Over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)



**Equivalent Circuit** 



Top View

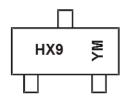
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP2900UW-7	SOT323	3,000/Tape & Reel
DMP2900UW-13	SOT323	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# Marking Information



 $HX9 = Product Type Marking Code YM = Date Code Marking Y or <math>\overline{Y} = Year (ex: I = 2021)$  M = Month (ex: 9 = September)

#### Date Code Key

Year	2018		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	F		I	J	K	L	М	N	0	Р	R	S
Month	.lan	Feb	Mar	Δnr	May	Jun	Jul	Διια	Sen	Oct	Nov	Dec
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-20	٧		
Gate-Source Voltage	$V_{GSS}$	±6	V		
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	lo	-0.6 -0.5	А		
Maximum Body Diode Forward Current (Note 6)	Is	-0.45	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	)		I <sub>DM</sub>	-2.5	Α

# **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P <sub>D</sub>	0.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	393	°C/W
Total Power Dissipation (Note 6)		PD	0.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RөJA	272	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$		
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_	_	-100	nA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±2.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.5	_	-1.0	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$		
			_	0.75		$V_{GS} = -4.5V, I_{D} = -430mA$		
Static Drain-Source On-Resistance	RDS(ON)	_	_	1.05	Ω	$V_{GS} = -2.5V, I_{D} = -300mA$		
				1.5		$V_{GS} = -1.8V, I_{D} = -150mA$		
Diode Forward Voltage	$V_{SD}$	_	_	-1.2	V	$V_{GS} = 0V, I_{S} = -150mA$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	Ciss	l	49		pF	.,		
Output Capacitance	Coss	-	12	_	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V, -f = 1.0MHz		
Reverse Transfer Capacitance	Crss	_	3.4	_	pF	T = T.OIVII IZ		
Total Gate Charge	Qg	_	0.7	_	nC	45)/ )/ 40)/		
Gate-Source Charge	Qgs	_	0.1	_	nC	$V_{GS} = -4.5V, V_{DS} = -10V,$ $I_{D} = -250 \text{mA}$		
Gate-Drain Charge	Q <sub>gd</sub>	_	0.1	_	nC	ID = -250IIIA		
Turn-On Delay Time	tD(ON)	_	16	_	ns			
Turn-On Rise Time	t <sub>R</sub>	_	15	_	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$		
Turn-Off Delay Time	tD(OFF)	_	213	_	ns	$R_L = 47\Omega$ , $R_G = 10\Omega$ ,		
Turn-Off Fall Time	tr	-	89	_	ns	I <sub>D</sub> = -200mA		
Reverse Recovery Time	t <sub>RR</sub>	1	10.5	_	ns	I_ 1.00 di/dt = 1000/:		
Reverse Recovery Charge	$Q_{RR}$	_	1.8	_	nC	IF = -1.0A, di/dt = 100A/µs		

 Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing. Notes:

25°C

2

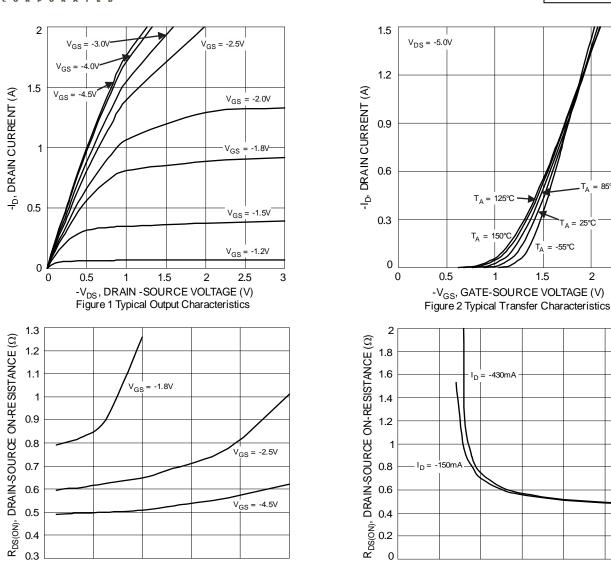
2.5

6

= -55°C

1.5





 ${}^{-}\mathrm{V}_{\mathrm{GS'}}$  GATE-SOURCE VOLTAGE (V) Figure 4 Typical Drain-Source On-Resistance -I<sub>D</sub>, DRAIN SOURCE CURRENT (A) Figure 3 Typical On-Resistance vs. vs. Gate-Source Voltage Drain Current and Gate Voltage

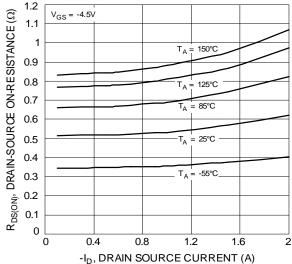


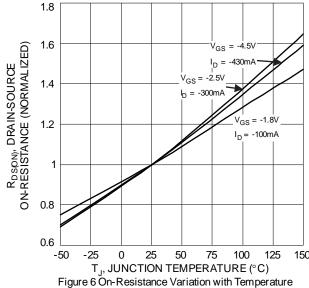
Figure 5 Typical On-Resistance vs.

Drain Current and Temperature

8.0

1.2

1.6

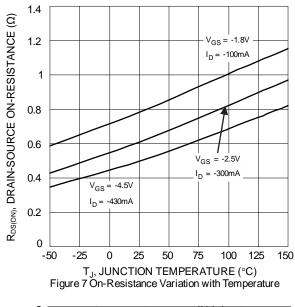


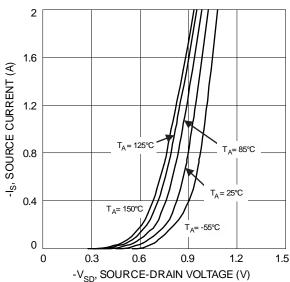
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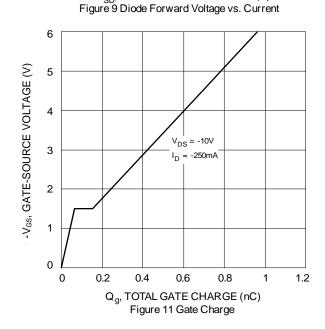
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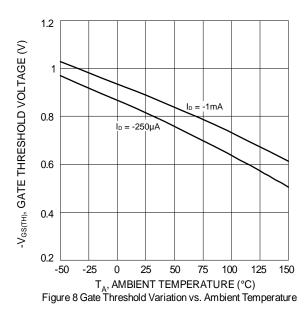
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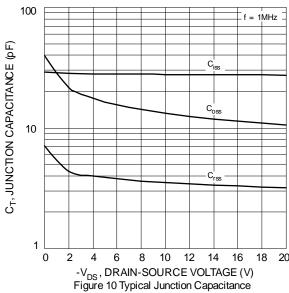


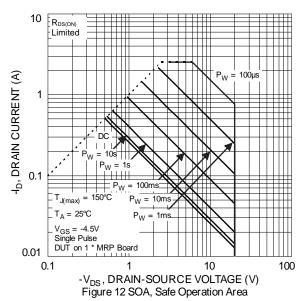




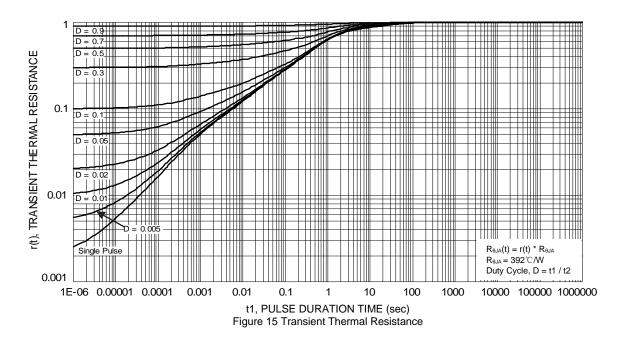










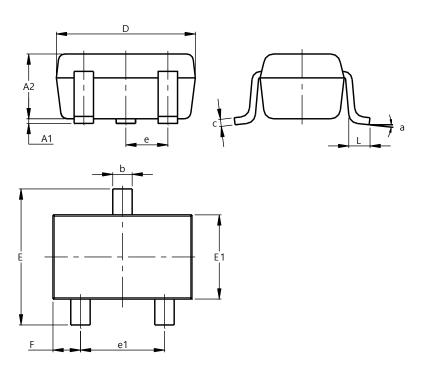




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT323**

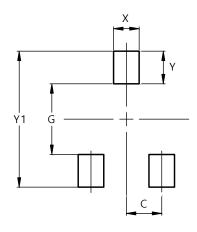


SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	(	).650 B	SC				
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT323**



Dimensions	Value (in mm)		
С	0.650		
G	1.300		
Х	0.470		
Υ	0.600		
Y1	2.500		



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